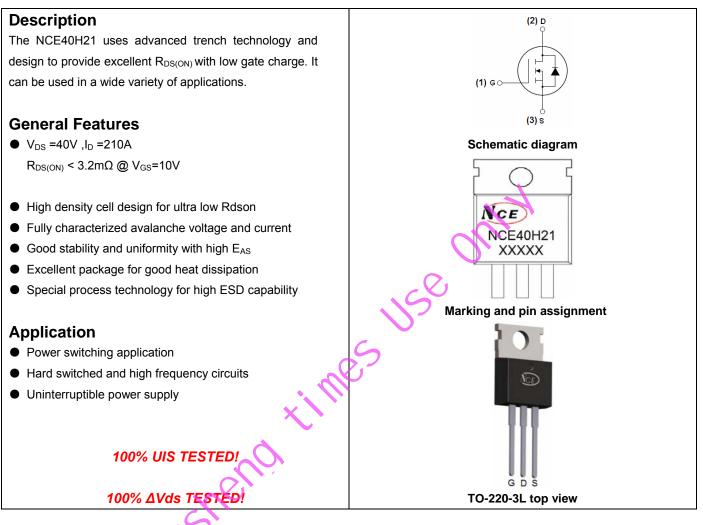


NCE40H21

NCE N-Channel Enhancement Mode Power MOSFET



Package Marking and Ordering Information

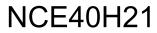
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40H21	NCE40H21	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	210	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	148	A
Pulsed Drain Current	I _{DM}	840	A
Maximum Power Dissipation	PD	310	W
Derating factor		2.07	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	2500	mJ
Operating Junction and Storage Temperature Range	T_{J},T_{STG}	-55 To 175	°C







Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.48	°C/W
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Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.3	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	- 1	2.3	3.2	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =20A	-	100	-	S
Dynamic Characteristics (Note4)		0				
Input Capacitance	Clss		-	10331	-	PF
Output Capacitance	Coss	V _{DS} =25V V _{GS} =0V, F=1.0MHz	-	1160	-	PF
Reverse Transfer Capacitance	C _{rss}		-	1045	-	PF
Switching Characteristics (Note 4)		6				
Turn-on Delay Time	t _{d(on)}	0,2	-	41	-	nS
Turn-on Rise Time	tr 📢	V _{DD} =30V,R _L =15Ω,	-	40	-	nS
Turn-Off Delay Time	t _{d(off)}	R _G =2.5Ω,V _{GS} =10V	-	145	-	nS
Turn-Off Fall Time	t _f		-	65	-	nS
Total Gate Charge	Qg		-	239	-	nC
Gate-Source Charge	, Q _{gs}	I _D =20A,V _{DD} =20V,V _{GS} =10V	-	23.5	-	nC
Gate-Drain Charge	Q _{gd}		-	49.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	0.85	1.2	V
Diode Forward Current (Note 2)	ls		-	-	210	А
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A	-	55		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	90		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				y LS+LD)

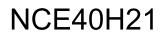
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, t \leq 10 sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25 Ω

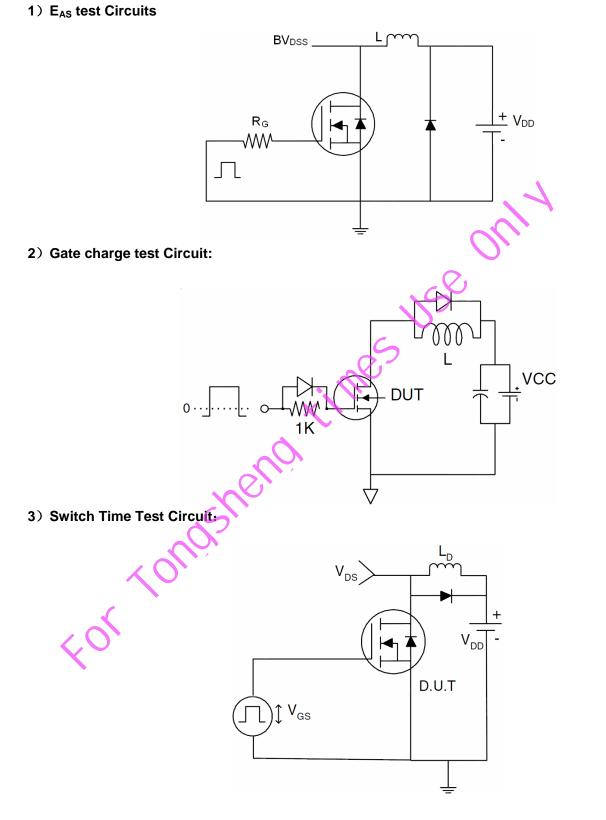


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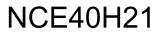
Pb Free Product



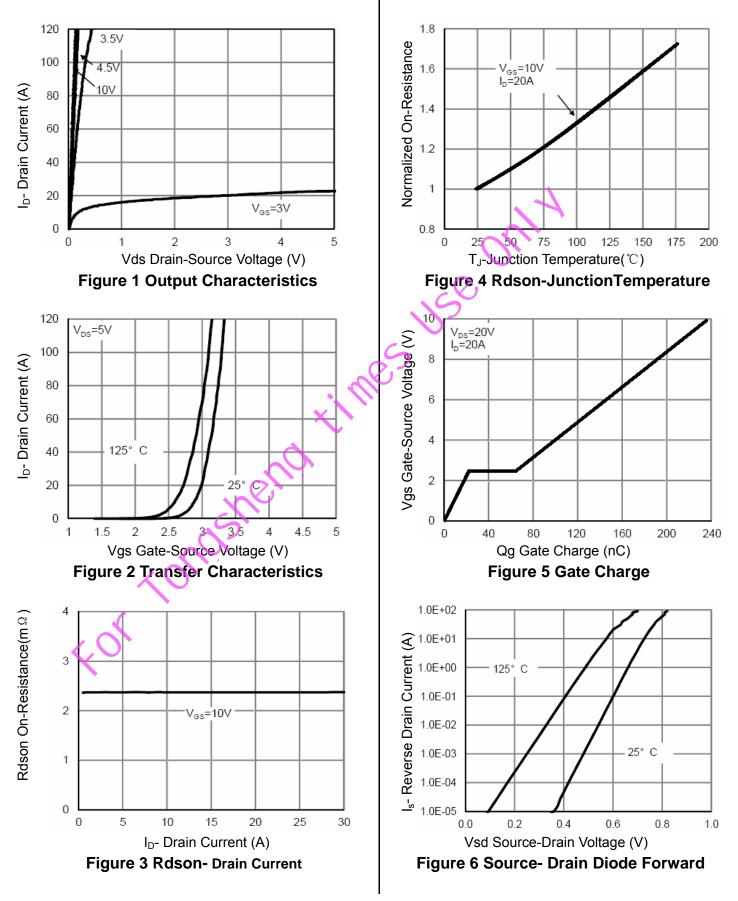
Test circuit







Typical Electrical and Thermal Characteristics (Curves)

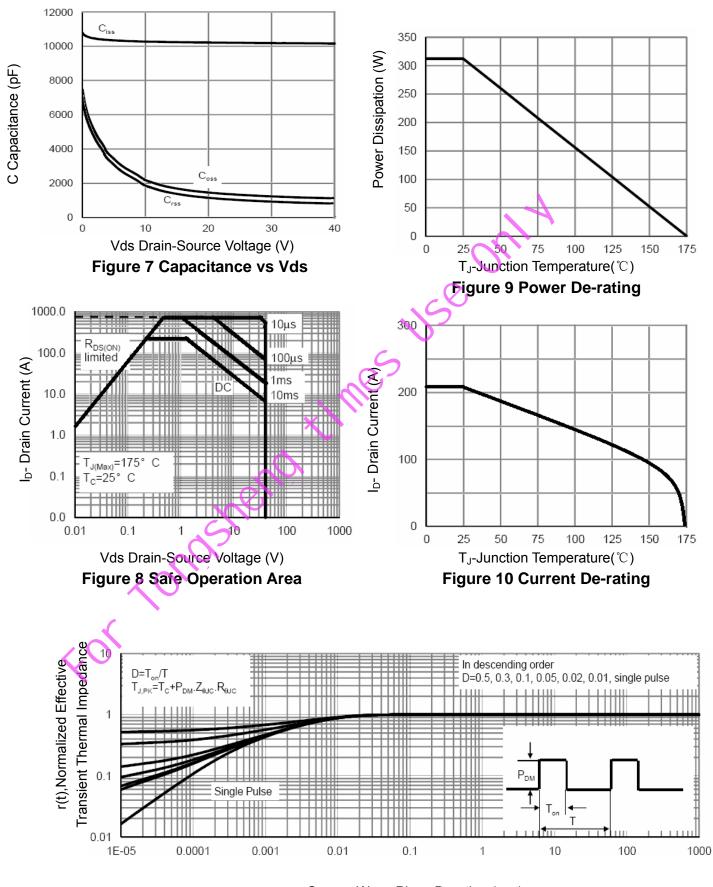




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Square Wave Pluse Duration (sec) Figure 11 Normalized Maximum Transient Thermal Impedance

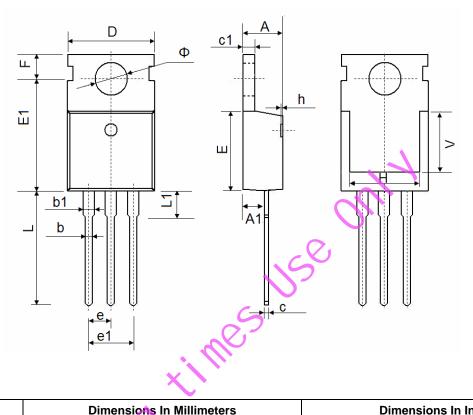


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NCE40H21

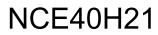
TO-220-3L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
с	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
e	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	







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